

3V DCS LOW NOISE AMPLIFIER

Typical Applications

- LNA for DCS 1800/1900 Handsets
- IF or RF Buffer Amplifiers

- Driver Stage for Power Amplifiers
- Oscillator Loop Amplifiers

1.59-1.61

Product Description

The RF2375 is a general purpose, low-cost, high performance, low noise amplifier designed for operation from a 2.7V to 4V supply with low current consumption. The attenuation of the device is controlled when in power down mode, providing a known gain step. The input IP3 can be set with an external resistor to allow maximizing of the dynamic range of the receiver design. The RF2375 is available in a small industry-standard SOT-23-8 lead surface mount package, enabling compact designs which conserve board space. PTAT (Proportional To Absolute Temperature) bias currents are used to bias the LNA.

0.15-0.05 0.365 TEXT* Ш 0.650 1.44 1.04 2.60 3.00 0.127 3°MAX 0°MIN *When Pin 1 is in upper left, text reads downward (as shown). 0.35

Package Style: SOT-23-8

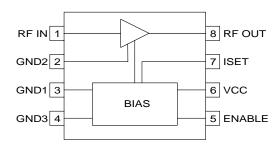
Optimum Technology Matching® Applied

Si BJT

GaAs HBT

GaAs MESFET

Si Bi-CMOS SiGe HBT ☐ Si CMOS



Functional Block Diagram

Features

- 700MHz to 2000MHz Operation
- 2.7V to 3.6V Single Supply
- -5dBm Input IP₃ at 5.3mA
- 18dB Gain at 1950MHz
- 2.5dB Noise Figure
- 25dB Gain Step

Ordering Information

RF2375 3V DCS Low Noise Amplifier RF2375 PCBA Fully Assembled Evaluation Board

RF Micro Devices, Inc. 7625 Thorndike Road Greensboro, NC 27409, USA

Tel (336) 664 1233 Fax (336) 664 0454 http://www.rfmd.com

Rev A2 010126 4-227

Absolute Maximum Ratings

| Parameter | Rating | Unit |
|-------------------------------|-------------|------|
| Supply Voltage | 4.0 | V |
| Supply Current | 20 | mA |
| Operating Ambient Temperature | -40 to +85 | °C |
| Storage Temperature | -40 to +150 | °C |



RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

| Parameter | Specification | | Unit | Condition | | |
|---------------------|---------------|-------------|-------|-----------|---|--|
| Farameter | Min. | Тур. | Max. | Ollit | Condition | |
| Overall | | | | | T=27°C, V _{CC} =2.7V, Freq=1950MHz | |
| Frequency Range | | 700 to 2000 | | MHz | | |
| LNA Performance | | | | | | |
| Gain | 16 | 18 | | dB | | |
| Noise Figure | | 2.5 | | dB | | |
| Input IP3 | -6 | -5 | | dBm | At 5.3mA | |
| Input P1dB | | -18.5 | | dBm | | |
| Input VSWR | | 2:1 | | dB | | |
| Output VSWR | | | 1.5:1 | dB | | |
| Off Mode Gain | | -7 | | dB | | |
| Power Control | | | | | | |
| Power "ON" Voltage | | CMOS High | | V | Voltage on ENABLE | |
| Power "OFF" Voltage | | CMOS Low | | V | Voltage on ENABLE | |
| Current into ENABLE | | | 1 | μΑ | V _{ENABLE} =2.7V | |
| Power Supply | | | | | | |
| Operating Voltage | | 2.7 to 3.6 | | V | | |
| Operating Current | | 5.3 | 7 | mA | V_{CC} =2.7V, R_{ISET} =15k Ω | |
| Leakage Current | | | 1 | μΑ | V _{ENABLE} =0V | |

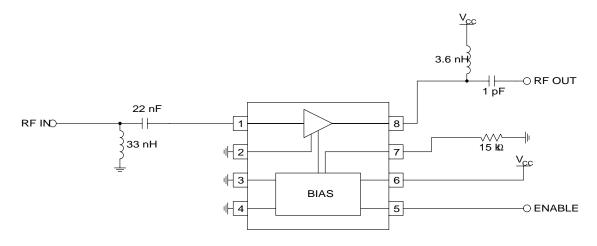
4-228 Rev A2 010126

RF2375

| Pin | Function | Description | Interface Schematic |
|-----|----------|---|---------------------|
| 1 | RF IN | RF input pin. This pin is not internally DC blocked and requires an external blocking capacitor. The input impedance of this pin is internally matched to 50Ω using feedback. | |
| 2 | GND2 | Ground connection for the bias circuits. | |
| 3 | GND1 | Ground connection for the LNA. Keep traces physically short and connect immediately to ground plane for best performance. | |
| 4 | GND3 | Same as pin 3. | |
| 5 | ENABLE | Power down control. This is a CMOS input. When this pin is CMOS "high" the device is enabled. When the level is CMOS "low" the device is shut off and a controlled attenuator is turned on. | |
| 6 | VCC | Power supply for the bias circuits. | |
| 7 | ISET | This pin sets the current for the device. A resistor to ground of $15k\Omega$ provides a current of $5.3mA$. | |
| 8 | RF OUT | RF output pin. The output impedance of this pin is internally matched to 50Ω using feedback. Bias for the LNA is provided through this pin, hence it should be connected to VCC through an inductor. | |

Preliminary

Application Schematic

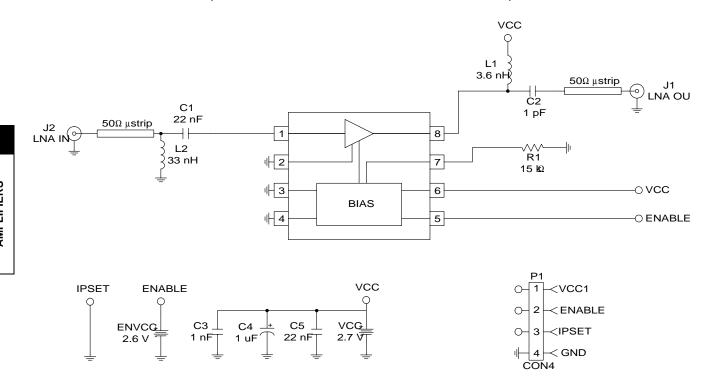


Rev A2 010126 4-229

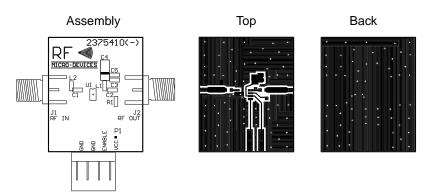
4

Evaluation Board Schematic RF = 1950MHz

(Download Bill of Materials from www.rfmd.com.)



Evaluation Board Layout Board Size 1.0" x 1.0" Board Thickness 0.031", FR-4



4-230 Rev A2 010126